

isc N-Channel MOSFET Transistor

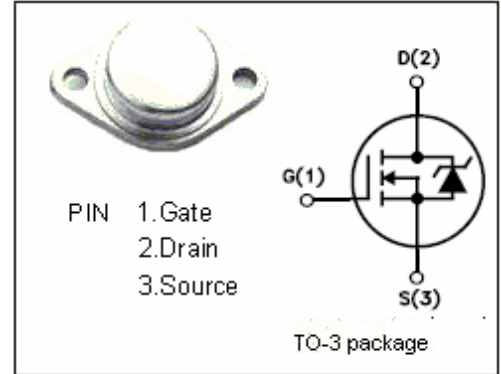
55N10

DESCRIPTION

- Drain Current  $I_D = 55A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 100V(\text{Min})$
- Fast Switching Speed

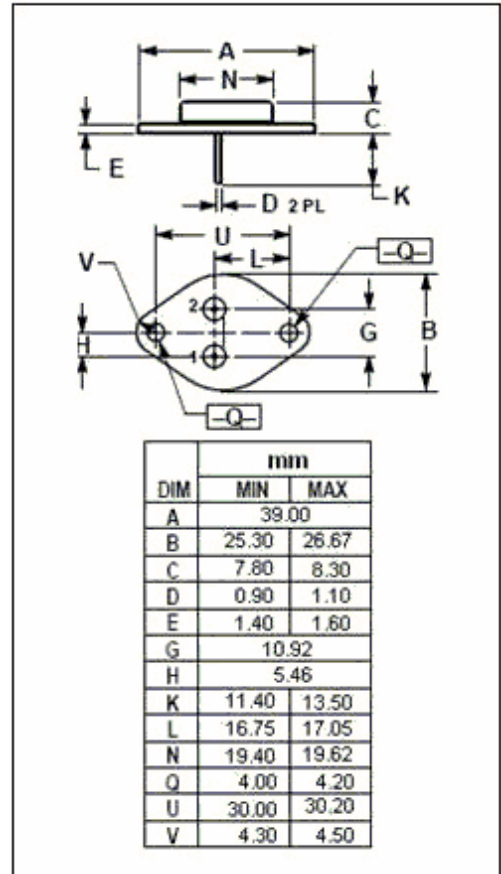
APPLICATIONS

- General purpose power amplifier



ABSOLUTE MAXIMUM RATINGS( $T_C = 25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS} = 0$ )	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $T_C = 25^\circ C$	55	A
$I_{D(puls)}$	Pulse Drain Current	275	A
$P_{tot}$	Total Dissipation@ $T_C = 25^\circ C$	250	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.5	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$

**isc N-Channel MOSFET Transistor****55N10**• ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	100			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
$V_{SD}$	Diode Forward On-Voltage	$I_F=55\text{A}; V_{GS}=0$			4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=30\text{A}$			0.025	$\Omega$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}= \pm 20\text{V}; V_{DS}=0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=100\text{V}; V_{GS}=0$			10	$\mu\text{A}$
$C_{iss}$	Input Capacitance	$V_{DS}=25\text{V};$ $V_{GS}=0\text{V};$ $f_T=1\text{MHz}$			5000	pF
$C_{rss}$	Reverse Transfer Capacitance				1000	
$C_{oss}$	Output Capacitance				2500	